

AMENDMENTS TO THE ABSTRACT:

Please amend the Abstract as follows:

In a thin film transistor (1), a gate insulating layer (4) is formed on a gate electrode (3) formed on an insulating substrate (2). Formed on the gate insulating layer (4) is a semiconductor layer (5). Formed on the semiconductor layer (5) are a source electrode (6) and a drain electrode (7). A protective layer (8) covers them, so that the semiconductor layer (5) is blocked from an atmosphere. The semiconductor layer (5) (active layer) is made of, e.g., a semiconductor containing polycrystalline ZnO to which, e.g., a group V element is added. ~~The protective layer (8) thus formed causes decrease of a surface level of the semiconductor layer (5). This eliminates a depletion layer spreading therewithin. Accordingly, the ZnO becomes an n-type semiconductor indicating an intrinsic resistance, with the result that too many free electrons are generated.~~ However, the added element works on the ZnO as an accepter impurity, so that the free electrons are reduced. ~~This decreases a gate voltage required for removal of the free electrons, so that the threshold voltage of the thin film transistor (1) becomes on the order of 0V.~~ This allows practical use of a semiconductor device which has an active layer made of zinc oxide and which includes an protective layer for blocking the active layer from an atmosphere.